

IN THE CLAIMS

1. (Original) A semiconductor device comprising:

a plurality of first memory cells for storing either one of first information and second information, arranged at points of intersection between a plurality of word lines and a plurality of first data lines;

a plurality of first dummy cells for storing said first information, arranged at points of intersection between said plurality of word lines and first dummy data lines; and

a plurality of second dummy cells for storing said second information, arranged at points of intersection between said plurality of word lines and second dummy data lines.

Claims 2-23 (Canceled)